

# GaAIAs-IR-Lumineszenzdiode (880 nm) GaAIAs Infrared Emitter (880 nm)

## SFH 487



### Wesentliche Merkmale

- GaAIAs-LED mit sehr hohem Wirkungsgrad
- Hohe Zuverlässigkeit
- Hohe Impulsbelastbarkeit
- Gute spektrale Anpassung an Si-Fotoempfänger
- Gehäusegleich mit SFH 309, SFH 409

### Anwendungen

- IR-Fernsteuerung von Fernseh-, Rundfunk- und Videogeräten, Lichtdimmern
- Lichtschranken bis 500 kHz
- Münzzähler
- Sensorik
- Diskrete Optokoppler

### Features

- Very highly efficient GaAIAs-LED
- High reliability
- High pulse handling capability
- Good spectral match to silicon photodetectors
- Same package as SFH 309, SFH 409

### Applications

- IR remote control for hifi and TV sets, video tape recorder, dimmers
- Light-reflection switches (max. 500 kHz)
- coin counters
- Sensor technology
- Discrete optocouplers

Typ Type	Bestellnummer Ordering Code	Gehäuse Package
SFH 487	Q62703-Q1095	3-mm-LED-Gehäuse (T1), klares violettes Epoxy-Gießharz, Anschlüsse im 2.54-mm-Raster (1/10"), Anodenkennzeichnung: kürzerer Anschluß 3 mm LED package (T1), violet-colored transparent epoxy resin, solder tabs lead spacing 2.54 mm (1/10"), anode marking: short lead
SFH 487-2	Q62703-Q2174	
SFH 487-3	Q62703-Q2175	

**Grenzwerte ( $T_A = 25\text{ °C}$ )****Maximum Ratings**

Bezeichnung Parameter	Symbol Symbol	Wert Value	Einheit Unit
Betriebs- und Lagertemperatur Operating and storage temperature range	$T_{op}; T_{stg}$	- 40 ... + 100	°C
Sperrspannung Reverse voltage	$V_R$	5	V
Durchlaßstrom Forward current	$I_F$	100	mA
Stoßstrom, $\tau \leq 10\ \mu\text{s}$ Surge current	$I_{FSM}$	2.5	A
Verlustleistung Power dissipation	$P_{tot}$	200	mW
Wärmewiderstand, freie Beinchenlänge max. 10 mm Thermal resistance, lead length between package bottom and PC-board max. 10 mm	$R_{thJA}$	375	K/W

**Kennwerte ( $T_A = 25\text{ °C}$ )****Characteristics**

Bezeichnung Parameter	Symbol Symbol	Wert Value	Einheit Unit
Wellenlänge der Strahlung Wavelength at peak emission $I_F = 100\text{ mA}$	$\lambda_{peak}$	880	nm
Spektrale Bandbreite bei 50% von $I_{max}$ , $I_F = 100\text{ mA}$ Spectral bandwidth at 50% of $I_{max}$	$\Delta\lambda$	80	nm
Abstrahlwinkel Half angle	$\varphi$	$\pm 20$	Grad deg.
Aktive Chipfläche Active chip area	$A$	0.09	mm <sup>2</sup>
Abmessungen der aktiven Chipfläche Dimension of the active chip area	$L \times B$ $L \times W$	$0.3 \times 0.3$	mm
Abstand Chipoberfläche bis Linsenscheitel Distance chip front to lens top	$H$	2.6	mm

Kennwerte ( $T_A = 25\text{ °C}$ )

Characteristics (cont'd)

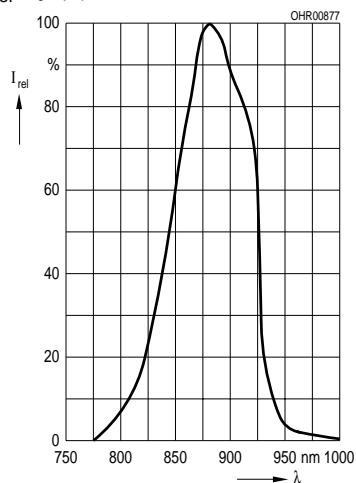
Bezeichnung Parameter	Symbol Symbol	Wert Value	Einheit Unit
Schaltzeiten, $I_e$ von 10% auf 90% und von 90% auf 10%, bei $I_F = 100\text{ mA}$ , $R_L = 50\ \Omega$ Switching times, $I_e$ from 10% to 90% and from 90% to 10%, $I_F = 100\text{ mA}$ , $R_L = 50\ \Omega$	$t_r, t_f$	0.6/0.5	$\mu\text{s}$
Kapazität Capacitance $V_R = 0\text{ V}$ , $f = 1\text{ MHz}$	$C_o$	15	pF
Durchlaßspannung Forward voltage $I_F = 100\text{ mA}$ , $t_p = 20\text{ ms}$ $I_F = 1\text{ A}$ , $t_p = 100\ \mu\text{s}$	$V_F$	1.5 (< 1.8) 3.0 (< 3.8)	V
Sperrstrom Reverse current $V_R = 5\text{ V}$	$I_R$	0.01 ( $\leq 1$ )	$\mu\text{A}$
Gesamtstrahlungsfluß Total radiant flux $I_F = 100\text{ mA}$ , $t_p = 20\text{ ms}$	$\Phi_e$	25	mW
Temperaturkoeffizient von $I_e$ bzw. $\Phi_e$ , $I_F = 100\text{ mA}$ Temperature coefficient of $I_e$ or $\Phi_e$ , $I_F = 100\text{ mA}$	$TC_I$	- 0.5	%/K
Temperaturkoeffizient von $V_F$ , $I_F = 100\text{ mA}$ Temperature coefficient of $V_F$ , $I_F = 100\text{ mA}$	$TC_V$	- 2	mV/K
Temperaturkoeffizient von $\lambda_{\text{peak}}$ , $I_F = 100\text{ mA}$ Temperature coefficient of $\lambda_{\text{peak}}$ , $I_F = 100\text{ mA}$	$TC_\lambda$	0.25	nm/K

**Gruppierung der Strahlstärke  $I_e$  in Achsrichtung**gemessen bei einem Raumwinkel  $\Omega = 0.01$  sr**Grouping of Radiant Intensity  $I_e$  in Axial Direction**at a solid angle of  $\Omega = 0.01$  sr

Bezeichnung Parameter	Symbol	Wert Value			Einheit Unit
		SFH 487	SFH 487-2	SFH 487-3	
Strahlstärke Radiant intensity $I_F = 100$ mA, $t_p = 20$ ms	$I_e$	> 12.5	> 20	31 ... 125	mW/sr
Strahlstärke Radiant intensity $I_F = 1$ A, $t_p = 100$ $\mu$ s	$I_{e \text{ typ.}}$	270	270	–	mW/sr

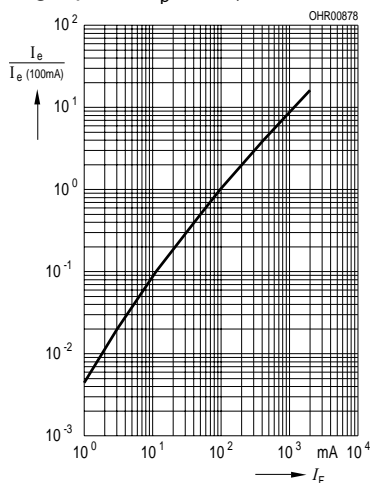
**Relative Spectral Emission**

$I_{rel} = f(\lambda)$



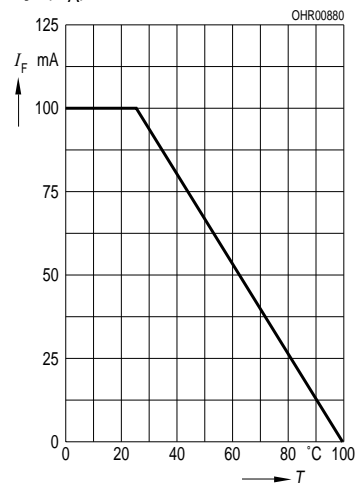
**Radiant Intensity**  $\frac{I_e}{I_e 100 \text{ mA}} = f(I_F)$

Single pulse,  $t_p = 20 \mu\text{s}$



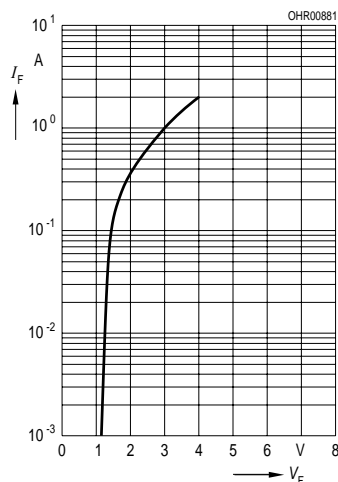
**Max. Permissible Forward Current**

$I_F = f(T_A)$



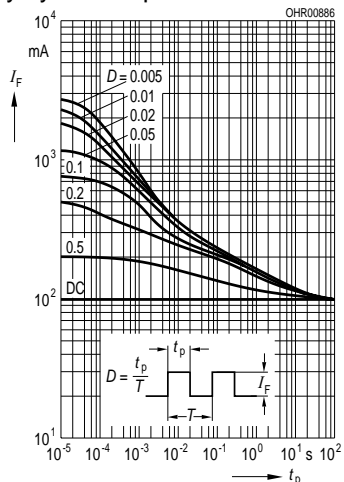
**Forward Current,  $I_F = f(V_F)$**

Single pulse,  $t_p = 20 \mu\text{s}$



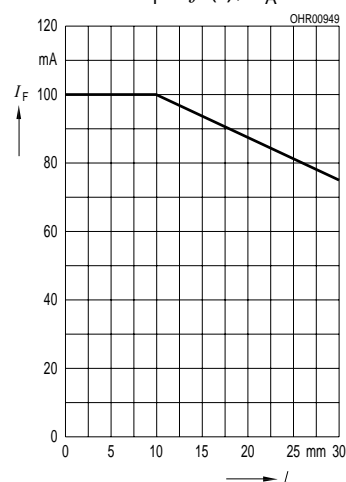
**Permissible Pulse Handling Capability**

$I_F = f(\tau)$ ,  $T_A = 25 \text{ }^\circ\text{C}$ , duty cycle  $D = \text{parameter}$

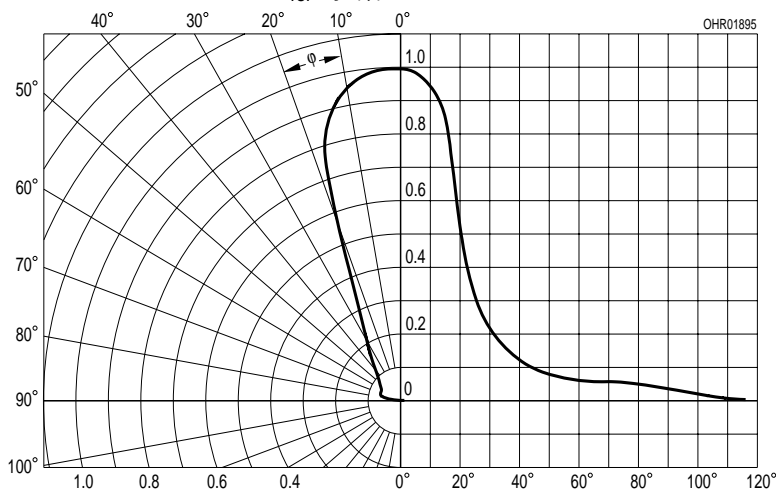


**Forward Current vs. Lead Length**

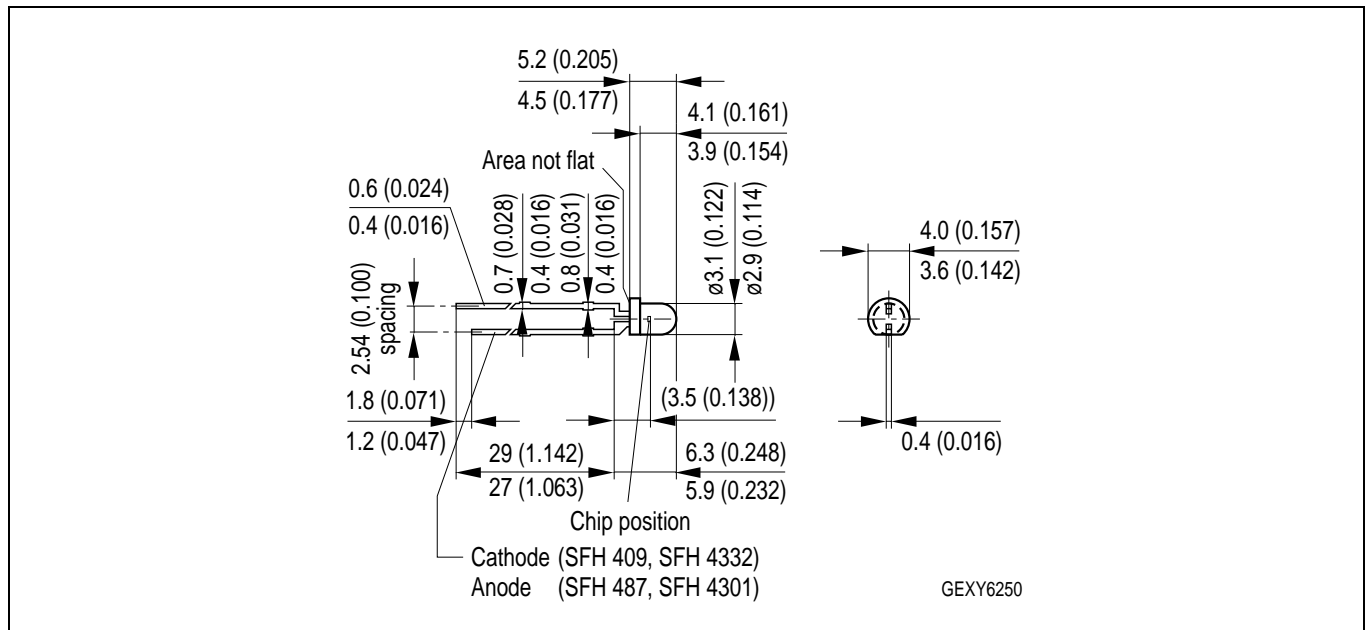
between the Package Bottom and the PC-Board  $I_F = f(l)$ ,  $T_A = 25 \text{ }^\circ\text{C}$



**Radiation Characteristics**  $I_{rel} = f(\varphi)$



## Maßzeichnung Package Outlines



Maße werden wie folgt angegeben: mm (inch) / Dimensions are specified as follows: mm (inch).

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Please use the recycling operators known to you. We can also help you – get in touch with your nearest sales office. By agreement we will take packing material back, if it is sorted. You must bear the costs of transport. For packing material that is returned to us unsorted or which we are not obliged to accept, we shall have to invoice you for any costs incurred.

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